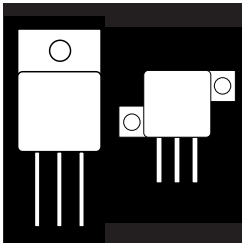


POWER MOSFETS IN HERMETIC ISOLATED JEDEC TO-254AA SIZE 6 DIE



**400V, 500V, N-Channel, Up To 24 Amp
Size 6 MOSFETs, High Energy Capability**

FEATURES

- Isolated Hermetic Metal Package
- Size 6 Die, High Energy
- Fast Switching, Low Drive Current
- Ease of Paralleling For Added Power
- Low $R_{DS(on)}$
- Available Screened To MIL-S-19500, TX, TXV And S Levels

DESCRIPTION

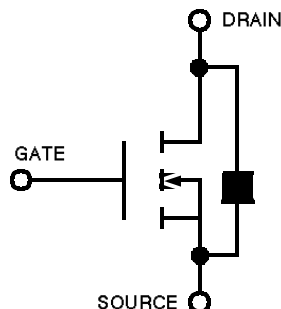
This series of hermetically packaged products feature the latest advanced MOSFET and packaging technology. They are ideally suited for Military requirements where small size, high performance and high reliability are required, and in applications such as switching power supplies, motor controls, inverters, choppers, audio amplifiers and high energy pulse circuits. This series also features avalanche high energy capability at elevated temperatures.

MAXIMUM RATINGS

PART NUMBER	V_{DS}	$R_{DS(on)}$	I_D (Amp)
OM6025SA	400	.23	24
OM6026SA	500	.30	22

3.1

SCHEMATIC



OM6025SA - OM6026SA

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	OM6025SA	OM6026SA	Units
V_{DS} Drain-Source Voltage	400	500	V
V_{DGR} Drain-Gate Voltage ($R_{GS} = 1\text{ M}$)	400	500	V
$I_D @ T_C = 25^\circ\text{C}$ Continuous Drain Current ²	24	22	A
I_{DM} Pulsed Drain Current ²	92	85	A
$P_D @ T_C = 25^\circ\text{C}$ Maximum Power Dissipation	165	165	W
Derate Above 25°C Ambient	.025	.025	W/ $^\circ\text{C}$
W_{DSS} (1) (2) Single Pulse Energy Drain To Source @ 25°C	1000	1200	mJ
T_J Operating and T_{stg} Storage Temperature Range	-55 to 150	-55 to 150	$^\circ\text{C}$
Lead Temperature (1/8" from case for 5 secs.)	275	275	$^\circ\text{C}$

Note 1: $V_{DD} = 50\text{V}$, $I_D =$ as noted

Note 2: Package Pin Limitation $I_D @ T_C = 25^\circ\text{C} = 25\text{ Amps}$

THERMAL RESISTANCE (MAXIMUM) at $T_A = 25^\circ\text{C}$

R_{thJC} Junction-to-Case	.76	$^\circ\text{C/W}$	
R_{thJA} Junction-to-Ambient	40	$^\circ\text{C/W}$	Free Air Operation
Derate Above 25°C Case	1.32	W/ $^\circ\text{C}$	

ELECTRICAL CHARACTERISTICS: OM6025SA (T_C = 25° unless otherwise noted)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V _{GS} = 0, I _D = 0.25 mA)	V _{(BR)DSS}	400	-	-	V _{dc}
Zero Gate Voltage Drain (V _{DS} = 400 V, V _{GS} = 0)	I _{BSS}	-	-	0.25	mAdc
(V _{DS} = 400 V, V _{GS} = 0, T _J = 125° C)		-	-	1.0	nAdc
Gate-Body Leakage Current, Forward (V _{GSF} = 20 V _{dc} , V _{DS} = 0)	I _{BSSF}	-	-	100	nAdc
Gate-Body Leakage Current, Reverse (V _{GSR} = 20 V _{dc} , V _{DS} = 0)	I _{BSSR}	-	-	100	nAdc

ON CHARACTERISTICS*

Gate-Threshold Voltage (V _{DS} = V _{GS} , I _D = 0.25 mA _{dc}) (T _J = 125° C)	V _{GS(th)}	2.0	3.0	4.0	V _{dc}
Static Drain-Source On-Resistance (V _{GS} = 10 V _{dc} , I _D = 12 A _{dc})	r _{DS(on)}	1.5	-	3.5	Ohm
Drain-Source On-Voltage (V _{GS} = 10 V _{dc}) (I _D = 24 A)	V _{DS(on)}	-	-	0.23	V _{dc}
Forward Transconductance (V _{DS} = 15 V _{dc} , I _D = 12 A _{dc})	g _{FS}	14	-	-	mhos

DYNAMIC CHARACTERISTICS

Input Capacitance (V _{DS} = 25 V, V _{GS} = 0, f = 1.0 MHz)	C _{iss}	-	5600	-	pF
Output Capacitance	C _{oss}	-	78	-	pF
Transfer Capacitance	C _{iss}	-	230	-	pF

SWITCHING CHARACTERISTICS

Turn-On Delay Time (V _{DD} = 250 V, I _D = 24 A, R _{gsm} = 4.3 ohms)	t _{d(on)}	-	70	-	ns
Rise Time	t _r	-	190	-	ns
Turn-Off Delay Time	t _{d(off)}	-	160	-	ns
Fall Time	t _f	-	160	-	ns
Total Gate Charge (V _{DS} = 400 V, I _D = 24 A, V _{GS} = 10 V)	Q _g	-	110	140	nC
Gate-Source Charge	Q _{gs}	-	20	-	nC
Gate-Drain Charge	Q _{gd}	-	55	-	nC

SOURCE DRAIN DIODE CHARACTERISTICS

Forward On-Voltage (I _S = 24 A, dI/dt = 100 A/μs)	V _{SD}	-	1.1	1.6	V _{dc}
Forward Turn-On Time	t _{bn}	-	**	-	ns
Reverse Recovery Time	t _{rr}	-	500	1000	ns

ELECTRICAL CHARACTERISTICS: OM6026SA (T_C = 25° unless otherwise noted)

Characteristic	Symbol	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage (V _{GS} = 0, I _D = 0.25 mA)	V _{(BR)DSS}	500	-	-	V _{dc}
Zero Gate Voltage Drain (V _{DS} = 500 V, V _{GS} = 0)	I _{BSS}	-	-	0.25	mAdc
(V _{DS} = 500 V, V _{GS} = 0, T _J = 125° C)		-	-	1.0	nAdc
Gate-Body Leakage Current, Forward (V _{GSF} = 20 V _{dc} , V _{DS} = 0)	I _{BSSF}	-	-	100	nAdc
Gate-Body Leakage Current, Reverse (V _{GSR} = 20 V _{dc} , V _{DS} = 0)	I _{BSSR}	-	-	100	nAdc

ON CHARACTERISTICS*

Gate-Threshold Voltage (V _{DS} = V _{GS} , I _D = 0.25 mA _{dc}) (T _J = 125° C)	V _{GS(th)}	2.0	3.0	4.0	V _{dc}
Static Drain-Source On-Resistance (V _{GS} = 10 V _{dc} , I _D = 11 A _{dc})	r _{DS(on)}	1.5	-	3.5	Ohm
Drain-Source On-Voltage (V _{GS} = 10 V _{dc}) (I _D = 22 A)	V _{DS(on)}	-	-	0.30	V _{dc}
Forward Transconductance (V _{DS} = 15 V _{dc} , I _D = 11 A _{dc})	g _{FS}	11	-	-	mhos

DYNAMIC CHARACTERISTICS

Input Capacitance (V _{DS} = 25 V, V _{GS} = 0, f = 1.0 MHz)	C _{iss}	-	5600	-	pF
Output Capacitance	C _{oss}	-	680	-	pF
Transfer Capacitance	C _{iss}	-	200	-	pF

SWITCHING CHARACTERISTICS

Turn-On Delay Time (V _{DD} = 250 V, I _D = 22 A, R _{gsm} = 4.3 ohms)	t _{d(on)}	-	70	-	ns
Rise Time	t _r	-	190	-	ns
Turn-Off Delay Time	t _{d(off)}	-	160	-	ns
Fall Time	t _f	-	160	-	ns
Total Gate Charge (V _{DS} = 400 V, I _D = 22 A, V _{GS} = 10 V)	Q _g	-	115	140	nC
Gate-Source Charge	Q _{gs}	-	20	-	nC
Gate-Drain Charge	Q _{gd}	-	60	-	nC

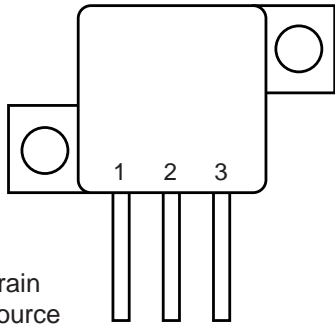
SOURCE DRAIN DIODE CHARACTERISTICS

Forward On-Voltage (I _S = 22A, dI/dt = 100 A/μs)	V _{SD}	-	1.1	1.6	V _{dc}
Forward Turn-On Time	t _{bn}	-	**	-	ns
Reverse Recovery Time	t _{rr}	-	500	1000	ns

* Indicates Pulse Test = 300 μsec, Duty Cycle = 2%
 ** Limited by circuit inductance

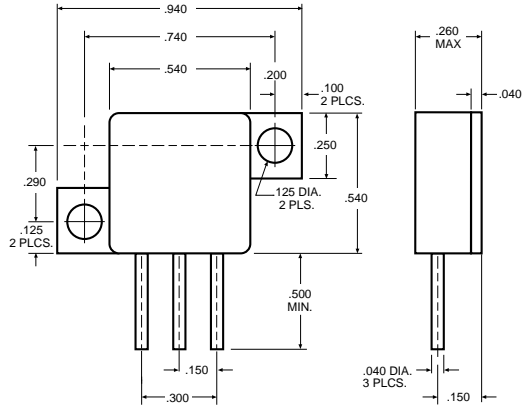
OM6025SC - OM6026SC

PIN CONNECTION

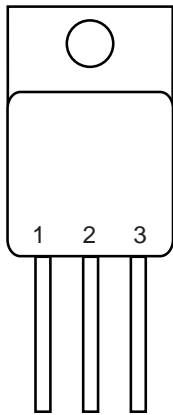


Pin 1: Drain
Pin 2: Source
Pin 3: Gate

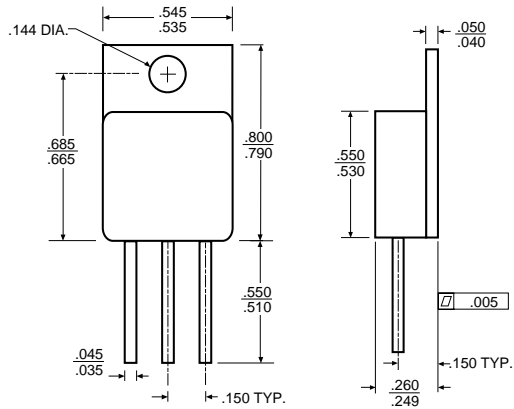
MECHANICAL OUTLINE



M-3S

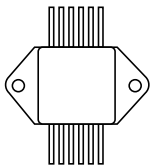


Pin 1: Drain
Pin 2: Source
Pin 3: Gate

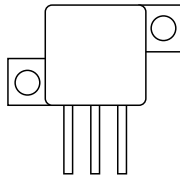


M-PAK

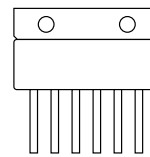
PACKAGE OPTIONS



MOD PAK



Z-TAB



6 PIN SIP

NOTES:

- Standard Products are supplied with glass feedthroughs. For ceramic feedthroughs, add the letter "C" to the part number. Example - OMXXXXCSA.
- MOSFETs are also available in Z-Tab, dual and quad pak styles - Please call the factory for more information.